

μ PA2822T1L

MOS FIELD EFFECT TRANSISTOR

R07DS0754EJ0100 Rev.1.00 May 25, 2012

Description

The μ PA2822T1L is N-channel MOS Field Effect Transistor designed for power management applications of a notebook computer and Lithium-Ion battery protection circuit.

Features

- $V_{DSS} = 30 \text{ V } (T_A = 25^{\circ}\text{C})$
- Low on-state resistance
 - $R_{DS(on)} = 2.6 \text{ m}\Omega$ MAX. ($V_{GS} = 10 \text{ V}$, $I_D = 34 \text{ A}$)
- 4.5V Gate-drive available
- Small surface mount package (8-pin HVSON (3333))
- Pb-free, Halogen Free

Ordering Information

Part No.	Lead Plating	Packing	Package
μPA2822T1L-E1-AT *1	Pure Sn (Tin)	Tape 3000 p/reel	8-pin HVSON (3333)
μPA2822T1L-E2-AT *1			typ. 0.028 g

Note: *1. Pb-free (This product does not contain Pb in external electrode and other parts.)

Absolute Maximum Ratings $(T_A = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to Source Voltage (V _{GS} = 0 V)	V _{DSS}	30	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	±20	V
Drain Current (DC) (T _C = 25°C)	I _{D(DC)}	±34	Α
Drain Current (pulse) *1	I _{D(pulse)}	±150	Α
Total Power Dissipation *2	P _{T1}	1.5	W
Total Power Dissipation (PW = 10 sec) *2	P _{T2}	3.8	W
Total Power Dissipation (T _C = 25°C)	P _{T3}	52	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C
Single Avalanche Current *3	I _{AS}	25	Α
Single Avalanche Energy *3	E _{AS}	62.5	mJ

Thermal Resistance

Channel to Ambient Thermal Resistance *2 R_{th(ch-A)} 83.3 °C/W Channel to Case (Drain) Thermal Resistance R_{th(ch-C)} 2.4 °C/W

Notes: *1. PW \leq 10 μ s, Duty Cycle \leq 1%

*2. Mounted on a glass epoxy board of 25.4 mm x 25.4 mm x 0.8 mmt

*3. Starting T_{ch} = 25°C, V_{DD} = 15 V, R_G = 25 Ω , V_{GS} = 20 \rightarrow 0 V, L = 100 μH

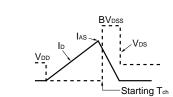
Electrical Characteristics (T_A = 25°C)

Item	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
Zero Gate Voltage Drain Current	I _{DSS}			1	μА	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$
Gate Leakage Current	I _{GSS}			±10	μА	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$
Gate Cut-off Voltage	$V_{GS(off)}$	1.0		2.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Forward Transfer Admittance *1	y _{fs}	16			S	$V_{DS} = 5 \text{ V}, I_{D} = 8.5 \text{ A}$
Drain to Source On-state	R _{DS(on)1}		1.9	2.6	mΩ	$V_{GS} = 10 \text{ V}, I_D = 34 \text{ A}$
Resistance *1	R _{DS(on)2}		3.5	7.5	mΩ	$V_{GS} = 4.5 \text{ V}, I_D = 8.5 \text{ A}$
Input Capacitance	C _{iss}		4660		pF	$V_{DS} = 10 \text{ V},$
Output Capacitance	Coss		1350		pF	$V_{GS} = 0 V$,
Reverse Transfer Capacitance	C _{rss}		1170		pF	f = 1 MHz
Turn-on Delay Time	t _{d(on)}		42		ns	$V_{DD} = 15 \text{ V}, I_D = 17 \text{ A},$
Rise Time	t _r		53		ns	$V_{GS} = 10 \text{ V},$
Turn-off Delay Time	t _{d(off)}		126		ns	$R_G = 10 \Omega$
Fall Time	t _f		85		ns	
Total Gate Charge	Q_G		83		nC	V _{GS} = 10 V,
			51		nC	$V_{GS} = 5 \text{ V}$
Gate to Source Charge	Q_{GS}		12		nC	$V_{DD} = 15 V$,
Gate to Drain Charge	Q_{GD}		28		nC	$I_D = 34 \text{ A}$
Body Diode Forward Voltage *1	$V_{F(S-D)}$		0.8		V	$I_F = 34 \text{ A}, V_{GS} = 0 \text{ V}$
Reverse Recovery Time	t _{rr}		61		ns	$I_F = 34 \text{ A}, V_{GS} = 0 \text{ V},$
Reverse Recovery Charge	Q _{rr}		64		nC	di/dt = 100 A/μs

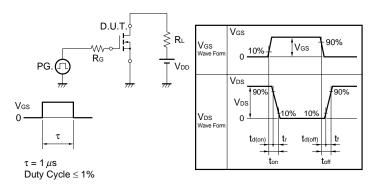
Note: *1. Pulsed

TEST CIRCUIT 1 AVALANCHE CAPABILITY

$\begin{array}{c|c} D.U.T. \\ \hline \\ R_G = 25 \Omega \\ \hline \\ V_{CS} = 20 \rightarrow 0 \end{array} \begin{array}{c} D.U.T. \\ \hline \\ \hline \\ V_{DD} \\ \hline \end{array}$



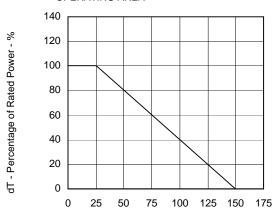
TEST CIRCUIT 2 SWITCHING TIME



TEST CIRCUIT 3 GATE CHARGE

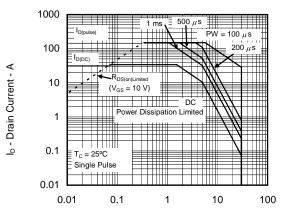
Typical Characteristics $(T_A = 25^{\circ}C)$

DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



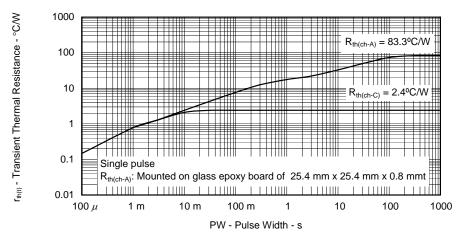
T_C - Case Temperature - °C

FORWARD BIAS SAFE OPERATING AREA

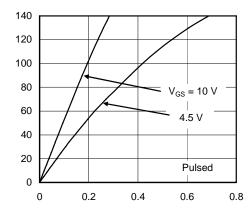


 $V_{\text{\scriptsize DS}}$ - Drain to Source Voltage - V

TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

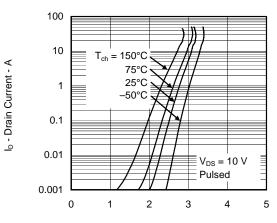


DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE



 $V_{\text{\scriptsize DS}}$ - Drain to Source Voltage - V

FORWARD TRANSFER CHARACTERISTICS



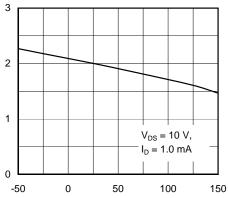
 V_{GS} - Gate to Source Voltage - V

I_D - Drain Current - A

V_{GS(off)} - Gate to Source Cut-off

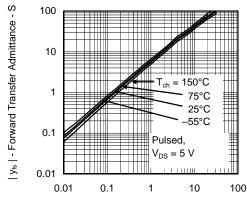
 $R_{\text{DS(on)}}$ - Drain to Source On-state Resistance - $m\Omega$

GATE TO SOURCE CUT-OFF VOLTAGE vs. **CHANNEL TEMPERATURE**



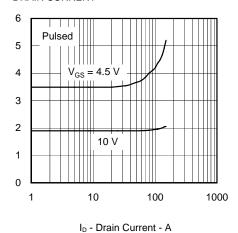
 T_{ch} - Channel Temperature - $^{\circ}C$

FORWARD TRANSFER ADMITTANCE vs. DRAIN **CURRENT**

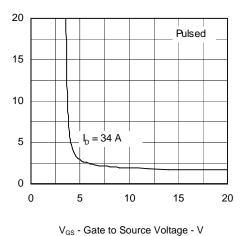


ID - Drain Current - A

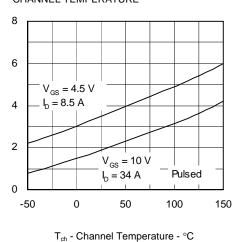
DRAIN TO SOURCE ON-STATE RESISTANCE vs. **DRAIN CURRENT**



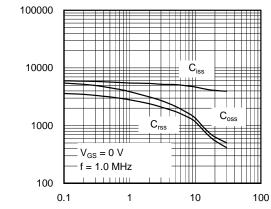
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



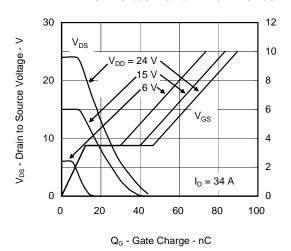
 V_{DS} - Drain to Source Voltage - V

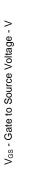
R_{DS(on)} - Drain to Source On-state Resistance - mΩ

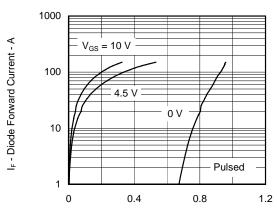
Ciss, Coss, Crss - Capacitance - pF

DYNAMIC INPUT/OUTPUT CHARACTERISTICS

SOURCE TO DRAIN DIODE FORWARD VOLTAGE



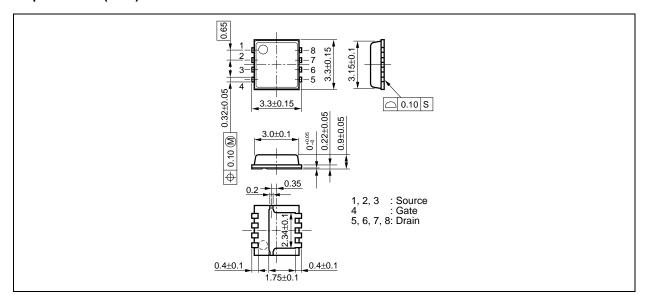




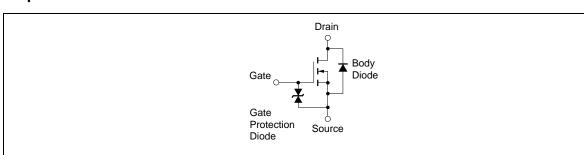
 $V_{\text{F(S-D)}}$ - Source to Drain Voltage - V

Package Drawings (Unit: mm)

8-pin HVSON (3333)



Equivalent Circuit



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

μ PA2822T1L Data Sheet

Ī			Description		
	Rev.	Date	Page	Summary	
Ī	1.00	May 25, 2012	_	First Edition Issued	

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